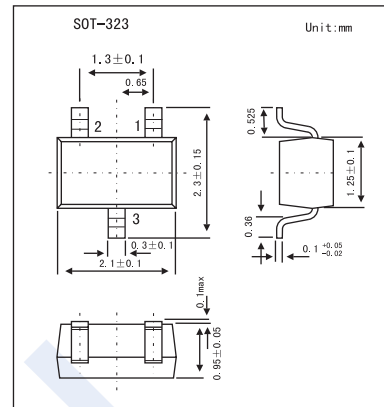
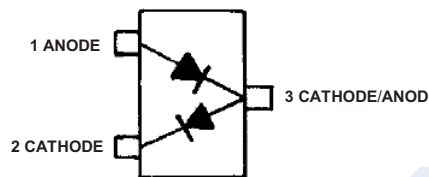


Silicon Epitaxial Schottky Barrier Type

1SS372

■ Features

- Small package
- Low forward voltage : $V_F = 0.23V$ (typ.) @ $I_F = 5mA$

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Maximum (Peak) reverse voltage	V_{RM}	15	V
Reverse voltage	V_R	10	V
Average forward current	I_O	100 *	mA
Maximum (Peak) forward current	I_{FM}	200 *	mA
Surge current (10ms)	I_{FSM}	1 *	A
Power dissipation	P	100	mW
Junction temperature	T_j	125	$^\circ C$
Storage temperature	T_{stg}	-55 to +125	$^\circ C$
Operating Temperature Range	T_{opr}	-40 to 100	$^\circ C$

*Unit Rating .Total Rating= Unit RatingX0.7

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Forward voltage	V_F	$I_F = 1mA$		0.18		V
		$I_F = 5mA$		0.23	0.30	
		$I_F = 100mA$		0.35	0.50	
Reverse current	I_R	$V_R = 10V$			20	μA
Total capacitance	C_T	$V_R = 0, f = 1MHz$		20	40	pF

■ Marking

Marking	N9
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